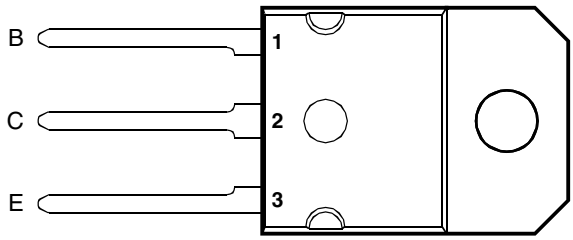
- **Designed for Complementary Use with the BD245 Series**
- **80 W at 25°C Case Temperature**
- **10 A Continuous Collector Current**
- **15 A Peak Collector Current**
- **Customer-Specified Selections Available**

SOT-93 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRAAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-emitter voltage (R_{BE} = 100 Ω)	BD246	V_{CER}	-55	V
	BD246A		-70	
	BD246B		-90	
	BD246C		-115	
Collector-emitter voltage (I_C = -30 mA)	BD246	V_{CEO}	-45	V
	BD246A		-60	
	BD246B		-80	
	BD246C		-100	
Emitter-base voltage		V_{EBO}	-5	V
Continuous collector current		I_C	-10	A
Peak collector current (see Note 1)		I_{CM}	-15	A
Continuous base current		I_B	-3	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	80	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3	W
Unclamped inductive load energy (see Note 4)		$½LI_C^2$	62.5	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	250	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle ≤ 10%.
2. Derate linearly to 150°C case temperature at the rate of 0.64 W/°C.
3. Derate linearly to 150°C free air temperature at the rate of 24 mW/°C.
4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = -0.4 A, R_{BE} = 100 Ω, $V_{BE(off)}$ = 0, R_S = 0.1 Ω, V_{CC} = -20 V.

electrical characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C = -30 mA (see Note 5)	I_B = 0	BD246	-45			V
				BD246A	-60			
				BD246B	-80			
				BD246C	-100			
I_{CES}	Collector-emitter cut-off current	V_{CE} = -55 V	V_{BE} = 0	BD246			-0.4	mA
		V_{CE} = -70 V	V_{BE} = 0	BD246A			-0.4	
		V_{CE} = -90 V	V_{BE} = 0	BD246B			-0.4	
		V_{CE} = -115 V	V_{BE} = 0	BD246C			-0.4	
I_{CEO}	Collector cut-off current	V_{CE} = -30 V	I_B = 0	BD246/246A			-0.7	mA
		V_{CE} = -60 V	I_B = 0	BD246B/246C			-0.7	
I_{EBO}	Emitter cut-off current	V_{EB} = -5 V	I_C = 0				-1	mA
h_{FE}	Forward current transfer ratio	V_{CE} = -4 V	I_C = -1 A	(see Notes 5 and 6)	40			
		V_{CE} = -4 V	I_C = -3 A		20			
		V_{CE} = -4 V	I_C = -10 A		4			
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_B = -0.3 A	I_C = -3 A	(see Notes 5 and 6)			-1	V
		I_B = -2.5 A	I_C = -10 A				-4	
V_{BE}	Base-emitter voltage	V_{CE} = -4 V	I_C = -3 A	(see Notes 5 and 6)			-1.6	V
		V_{CE} = -4 V	I_C = -10 A				-3	
h_{fe}	Small signal forward current transfer ratio	V_{CE} = -10 V	I_C = -0.5 A	f = 1 kHz	20			
$\|h_{fe}\|$	Small signal forward current transfer ratio	V_{CE} = -10 V	I_C = -0.5 A	f = 1 MHz	3			

NOTES: 5. These parameters must be measured using pulse techniques, t_p = 300 µs, duty cycle ≤ 2%.
6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1.56	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			42	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on}	Turn-on time	I_C = -1 A	$I_{B(on)}$ = -0.1 A	$I_{B(off)}$ = 0.1 A		0.2		µs
t_{off}	Turn-off time	$V_{BE(off)}$ = 3.7 V	R_L = 20 Ω	t_p = 20 µs, dc ≤ 2%		0.8		µs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN vs COLLECTOR CURRENT

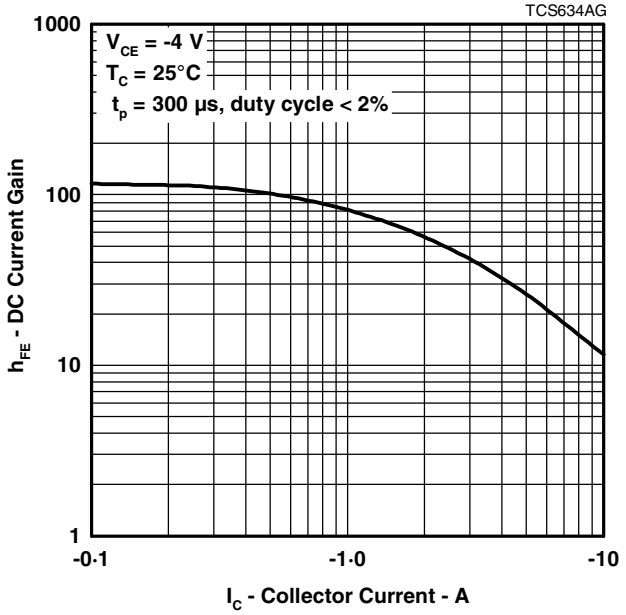


Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE vs BASE CURRENT

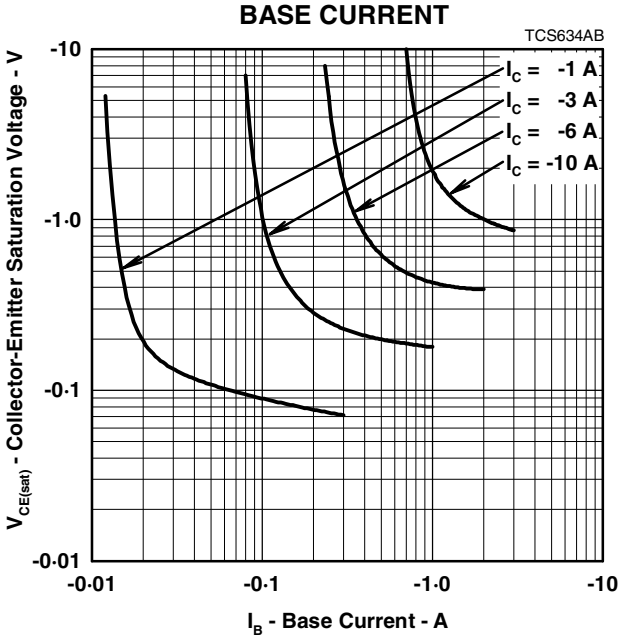


Figure 2.

BASE-EMITTER VOLTAGE vs COLLECTOR CURRENT

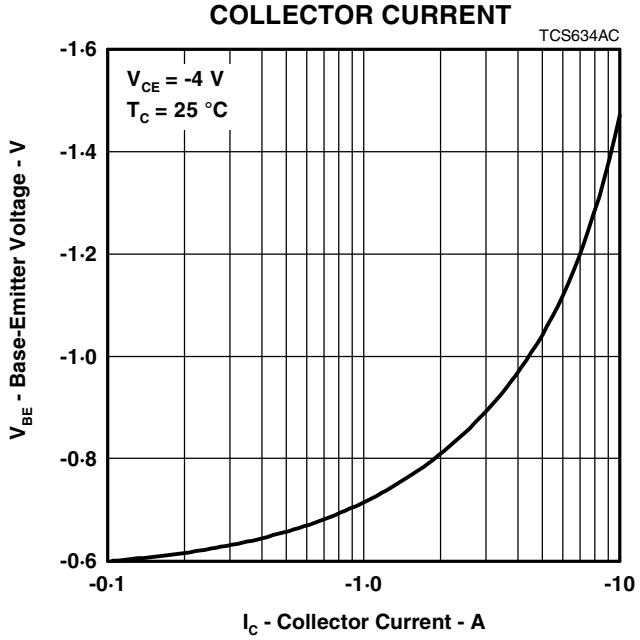


Figure 3.

MAXIMUM SAFE OPERATING REGIONS

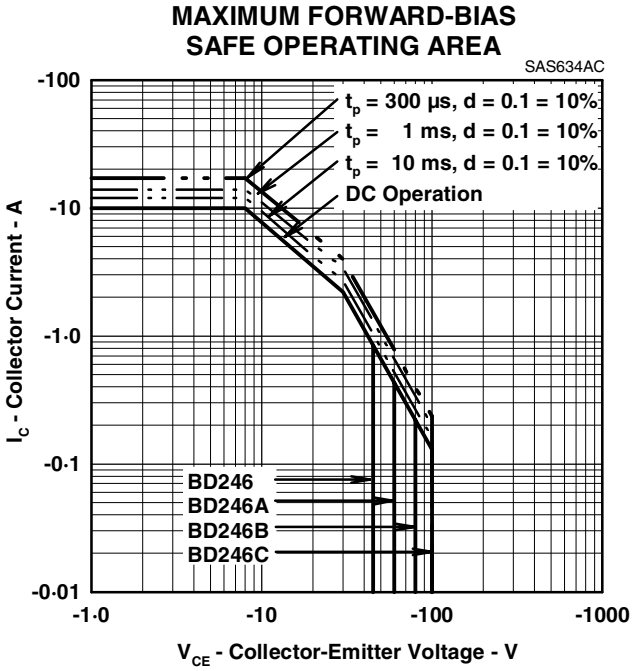


Figure 4.

THERMAL INFORMATION

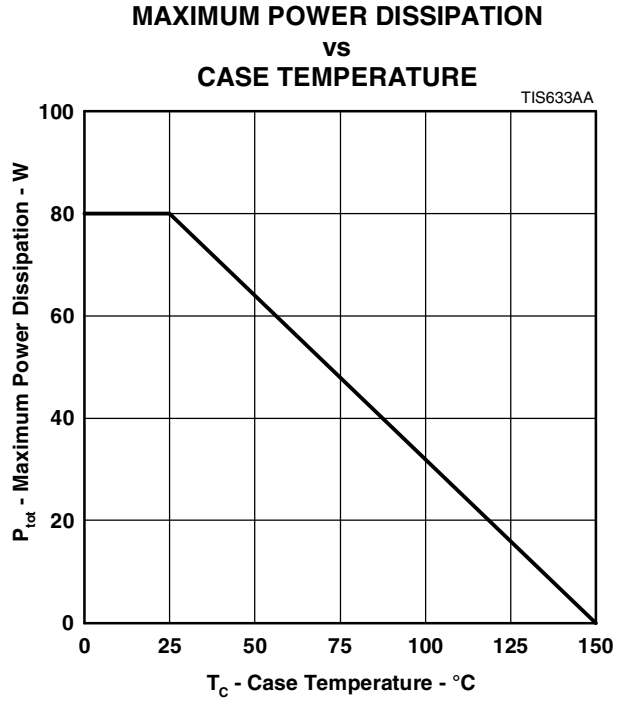


Figure 5.